



Sheet 1 of 23

PTO-1449 (Modified) U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO.	SERIAL NUMBER
	211.001-D4-US	10/727,742
	APPLICANT(S) Fazan et al.	
FILING DATE December 4, 2003	GROUP ART UNIT	

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JM	4,032,947	6/1977	Kesel et al.	257	214	
JM	3,997,799	12/1976	Baker	365	183	
JM	5,448,513	9/1995	Hu et al.	365	150	
JM	4,298,962	11/1981	Hamano et al.	365	182	
JM	3,439,214	4/1969	Kabell	315	11	
JM	6,081,443	6/2000	Morishita	365	149	
JM	6,111,778	8/2000	MacDonald et al.	365	149	

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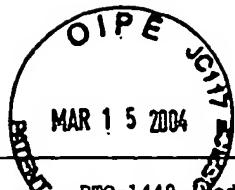
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
JM	FR 2 197 494	3/1974	French			
JM	EP 1 180 799	2/2002	European			
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JM	EP 0 694 977	1/1996	European			
JM	JP 02 294076	2/1991	Japanese			
JM	EP 1 237 193	9/2002	European			
JM	EP 0 878 804	11/1998	European			

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Sheet 2 of 23

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JM	EP 0 801 427	10/1997	European			
JM	EP 0 513 923	11/1992	European			

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STUDY SECTION (INTERVIEW)	

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<i>JM</i>	5,982,003	11/1999	Hu et al.	257	347	
<i>JM</i>	6,121,077	9/2000	Hu et al.	257	347	
<i>JM</i>	6,300,649	10/2001	Hu et al.	257	69	
<i>JM</i>	6,518,105	2/2003	Yang et al.	438	151	
<i>JM</i>	2002 0070411	6/2002	Vermandel et al.			

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<i>JM</i>	EP 0 731 972	11/2001	European			
<i>JM</i>	EP 0 362 961 B1	2/1994	European			
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<i>JM</i>	"The Multi-Stable Behaviour of SOI-NMOS Transistors at Low Temperatures", Tack et al., Proc. 1988 SOS/SOI Technology Workshop (Sea Palms Resort, St. Simons Island, GA, Oct. 1988), p.78
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<i>JM</i>	"Mechanisms of Charge Modulation in the Floating Body of Triple-Well nMOSFET Capacitor-less DRAMs", Villaret et al., Proceedings of the INFOS 2003, Insulating Films on Semiconductors, 13th Bi-annual Conference, June 18-20, 2003, Barcelona (Spain), (4 pages)

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JHC	2002/0051378	5/2002	Ohsawa			
JHC	2002/0076880	6/2002	Yamada et al.			
JHC	2002/0098643	7/2002	Kawanaka et al.			
JY	2002/0110018	8/2002	Ohsawa			
JY	2002/0114191	8/2002	Iwata et al.			
JY	2002/0130341	9/2002	Horiguchi et al.			
JY	2002/0160581	10/2002	Watanabe et al.			
JHC	2003/0003608	1/2003	Arikado et al.			
JHC	2003/0015757	1/2003	Ohsawa			
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JM	"FBC (Floating Body Cell) for Embedded DRAM on SOI, Inoh et al., 2003 Symposium on VLSI Circuits Digest of Technical Papers, June 2003 (2 pages)
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<i>JM</i>	"Design of a SOI Memory Cell", Stanojevic et al., IEEE Proc. 21 st International Conference on Microelectronics (MIEL '97), Vol. 1, NIS, Yugoslav, 14-17 September 1997, pp.297-300
<i>JM</i>	"Effects of Floating Body on Double Polysilicon Partially Depleted SOI Nonvolatile Memory Cell", Chan et al., IEEE Electron Device Letters, Vol. 24, No. 2, February 2003, pp.75-77
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<i>JM</i>	"One of Application of SOI Memory Cell – Memory Array", Lončar et al., IEEE Proc. 22 nd International Conference on Microelectronics (MIEL 2000), Vol. 2, NIŠ, Serbia, 14-17 May 2000, pp.455-458
<i>JM</i>	"A SOI Current Memory for Analog Signal Processing at High Temperature", Portmann et al., 1999 IEEE International SOI Conference, Oct. 1999, pp.18-19
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<i>JM</i>	"High-Performance Embedded SOI DRAM Architecture for the Low-Power Supply", Yamauchi et al., IEEE Journal of Solid-State Circuits, Vol. 35, No. 8, August 2000, pp.1169-1178
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<i>JM</i>	"A Capacitorless DRAM Cell on SOI Substrate", Wann et al., IEEE IEDM, 1993, pp.635-638

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<i>JKW</i>	"A Novel Silicon-On-Insulator (SOI) MOSFET for Ultra Low Voltage Operation", Assaderaghi et al., 1994 IEEE Symposium on Low Power Electronics, pp.58-59
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<i>S. Mai</i>	5/28/04

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PTO-1449 (Modified) U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO.	SERIAL NUMBER
	211.001-D4-US	10/727,742
	APPLICANT(S) Fazan et al.	
FILING DATE	GROUP ART. UNIT	
December 4, 2003		

U. S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
JK	EP 1 288 955 A2	3/2003	European			
JK	EP 1 280 205 A2	1/2003	European			
JK	EP 1 253 634 A2	10/2002	European			
JK	EP 1 241 708 A2	9/2002	European			
JK	EP 1 209 747 A2	5/2002	European			
JK	EP 1 204 147 A1	5/2002	European			
JK	EP 1 204 146 A1	5/2002	European			
JK	EP 1 179 850 A2	2/2002	European			
JK	EP 1 162 744 A1	12/2001	European			
JK	EP 1 162 663 A2	12/2001	European			
JK	EP 1 073 121 A2	1/2001	European			
JK	EP 0 993 037 A2	4/2000	European			
JK	EP 0 980 101 A2	2/2000	European			
JK	EP 0 971 360 A1	1/2000	European			

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	APPLICANT(S) Fazan et al.	
	FILING DATE December 4, 2003	GROUP ART UNIT

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
JM	EP 0 951 072 A1	10/1999	European		1	
JM	EP 0 933 820 A1	8/1999	European			
JM	EP 0 924 766 A2	6/1999	European			
JM	EP 0 920 059 A2	6/1999	European			
JM	EP 0 869 511 A2	10/1998	European			
JM	EP 0 860 878 A2	8/1998	European			
JM	EP 0 858 109 A2	8/1998	European			
JM	EP 0 844 671 B1	11/2002	European			
JM	EP 0 836 194 B1	5/2000	European			
JM	EP 0 788 165 A2	8/1997	European			
JM	EP 0 744 772 B1	8/2002	European			
JM	EP 0 739 097 A2	10/1996	European			
JM	EP 0 731 972 B1	11/2001	European			
JM	EP 0 727 822 B1	8/1999	European			

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JKL	EP 0 727 820 A1	8/1996	European			
JKL	EP 0 726 601 B1	9/2001	European			
JKL	EP 0 725 402 B1	9/2002	European			
JKL	EP 0 689 252 B1	8/2000	European			
JKL	EP 0 682 370 B1	9/2000	European			
JKL	EP 0 642 173 B1	7/1999	European			
JKL	EP 0 642 173 A1	3/1995	European			
JKL	EP 0 606 758 B1	9/2000	European			
JKL	EP 0 601 590 B1	4/2000	European			
JKL	EP 0 599 506 A1	6/1994	European			
JKL	EP 0 599 388 B1	8/2000	European			
JKL	EP 0 579 566 A2	1/1994	European			
JKL	EP 0 564 204 A2	10/1993	European			
JKL	EP 0 537 677 B1	8/1998	European			

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JKL	EP 0 465 961 B1	8/1995	European			
JKL	EP 0 366 882 B1	5/1995	European			
JKL	EP 0 362 961 B1	2/1994	European			
JKL	EP 0 359 551 B1	12/1994	European			
JKL	EP 0 354 348 A2	2/1990	European			
JKL	EP 0 350 057 B1	1/1990	European			
JKL	EP 0 333 426 B1	7/1996	European			
JKL	EP 0 300 157 B1	5/1993	European			
JKL	EP 0 253 631 B1	4/1992	European			
JKL	EP 0 245 515 B1	4/1997	European			
JKL	EP 0 207 619 B1	8/1991	European			
JKL	EP 0 202 515 B1	3/1991	European			
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	APPLICANT(S) Fazan et al.	
	FILING DATE December 4, 2003	GROUP ART UNIT

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JMC	2002/0036322	3/2002	Divakauni et al.			
JMC	5,446,299	8/1995	Acovic et al.			
JMC	5,568,356	10/1996	Schwartz			
JMC	5,627,092	5/1997	Alsmeyer et al.			
JMC	5,631,186	5/1997	Park et al.			
JMC	5,740,099	4/1998	Tanigawa			
JMC	5,877,978	3/1999	Morishita et al.			
JMC	5,930,648	7/1999	Yang			
JMC	5,939,745	8/1999	Park et al.			
JMC	5,943,258	8/1999	Houston et al.			
JMC	5,968,840	10/1999	Park et al.			
JMC	5,977,578	11/1999	Tang			
JMC	6,018,172	1/2000	Hidada et al.			

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	APPLICANT(S)	
	Fazan et al.	
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	December 4, 2003	

U. S. PATENT DOCUMENTS

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
JM	JP 62 272561	11/1987	Japanese			
JM	JP 8 274277	10/1996	Japanese			
JM	JP 9 82912	3/1997	Japanese			

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EXAMINER	S. Mai	DATE CONSIDERED	05/28/04
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PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. 211.001-D4-US	SERIAL NUMBER 10727,742
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	FILING DATE December 4, 2003	GROUP ART UNIT

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
<i>jk</i>	2002/0064913	5/2002	Adkisson et al.			
<i>jk</i>	2002/0072155	6/2002	Liu et al.			
<i>jk</i>	2002/0086463	7/2002	Houston et al.			
<i>jk</i>	2002/0089038	7/2002	Ning			
<i>jk</i>	2002/0180069	12/2002	Houston			
<i>jk</i>	2003/0102497	6/2003	Fried et al.			
<i>jk</i>	2003/0123279	7/2003	Aipperspach et al.			
<i>jk</i>	4,791,610	12/1988	Takemae			
<i>jk</i>	5,388,068	2/1995	Ghoshal et al.			
<i>jk</i>	5,446,299	8/1995	Acovic et al.			
<i>jk</i>	5,466,625	11/1995	Hsieh et al.			
<i>jk</i>	5,528,062	6/1996	Hsieh et al.			
<i>jk</i>	5,593,912	1/1997	Rajeevakumar			
<i>jk</i>	5,606,188	2/1997	Bronner et al.			

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JM	5,784,311	7/1998	Assaderaghi et al.			
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JM	5,886,376	3/1999	Acovic et al.			
JM	5,897,351	4/1999	Forbes			
JM	5,943,258	8/1999	Houston et al.			
JM	5,943,581	8/1999	Lu et al.			
JM	5,960,265	9/1999	Acovic et al.			
JM	6,096,598	8/2000	Furukawa et al.			
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JM	6,157,216	12/2000	Lattimore et al.			
JM	6,171,923	1/2001	Chi et al.			
JM	6,177,300	1/2001	Houston et al.			
JM	6,177,708	1/2001	Kuang et al.			

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JM	6,214,694	4/2001	Leobandung et al.			
JM	6,225,158	5/2001	Furukawa et al.			
JM	6,245,613	6/2001	Hsu et al.			
JM	6,297,090	10/2001	Kim			
JM	6,320,227	11/2001	Lee et al.			
JM	6,333,532	12/2001	Davari et al.			
JM	6,350,653	2/2002	Adkisson et al.			
JM	6,403,435	6/2002	Kang et al.			
JM	6,424,011	7/2002	Assaderaghi et al.			
JM	6,424,016	7/2002	Houston			
JM	6,429,477	8/2002	Mandelman et al.			
JM	6,440,872	8/2002	Mandelman et al.			
JM	6,441,435	8/2002	Chan			
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FOREIGN PATENT DOCUMENTS

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
<i>JL</i>	JP 11 87649	3/1999	Japanese			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

GRANT REC'D. (including interest, etc.)

EXAMINER	S. Mai	DATE CONSIDERED	05/08/04
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JKL	6,650,565	11/2003	Ohsawa			
JKL	6,632,723	10/2003	Watanabe et al.			
JKL	6,621,725	9/2003	Ohsawa			
JKL	6,617,651	9/2003	Ohsawa			
JKL	6,531,754	3/2003	Nagano et al.			
JKL	2002/0036322	3/2002	Divakauni et al.			

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
JKL	2003-243528	8/2003	Japanese			X
JKL	2002-94027	3/2002	Japanese			X
JKL	2002-176154	6/2002	Japanese			X
JKL	2002-246571	8/2002	Japanese			X
JKL	2002-329795	11/2002	Japanese			X
JKL	2002-343886	11/2002	Japanese			X
JKL	2002-353080	12/2002	Japanese			X
JKL	2003-31693	1/2003	Japanese			X
JKL	2003-86712	3/2003	Japanese			X

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JKL	DRAM Design Using the Taper-Isolated Dynamic RAM Cell, Leiss et al., IEEE Transactions on Electron Devices, Vol. ED-29, No. 4, April 1982, pp707-714

EXAMINER	DATE CONSIDERED
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JM	2003-100900	4/2003	Japanese			X
JM	2003-132682	5/2003	Japanese			X
JM	2003-203967	7/2003	Japanese			X
JM	2003-243528	8/2003	Japanese			X
JM	09046688	2/1997	Japanese			X
JM	JP 8-213624	8/1996	Japanese			X
JM	JP 3-171768	7/1991	Japanese			X

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